§ 98.87 Records that must be retained.

(a) If a CEMS is used to measure CO\textsubscript{2} emissions, then in addition to the records required by §98.3(g), you must retain under this subpart the records required for the Tier 4 Calculation Methodology in §98.37.

(b) If a CEMS is not used to measure CO\textsubscript{2} emissions, then in addition to the records required by §98.3(g), you must retain the records specified in this paragraph (b) for each portland cement manufacturing facility.

(1) Documentation of monthly calculated kiln-specific clinker CO\textsubscript{2} emission factor.

(2) Documentation of quarterly calculated kiln-specific CKD CO\textsubscript{2} emission factor.

(3) Measurements, records and calculations used to determine reported parameters.

[75 FR 66461, Oct. 28, 2010]

§ 98.88 Definitions.

All terms used in this subpart have the same meaning given in the Clean Air Act and subpart A of this part.

Subpart I—Electronics Manufacturing

SOURCE: 75 FR 74818, Dec. 1, 2010, unless otherwise noted.

§ 98.90 Definition of the source category.

(a) The electronics manufacturing source category consists of any of the production processes listed in paragraphs (a)(1) through (a)(5) of this section that use fluorinated GHGs or N\textsubscript{2}O. Facilities that may use these processes include, but are not limited to, facilities that manufacture micro-electromechanical systems (MEMS), liquid crystal displays (LCDs), photovoltaic cells (PV), and semiconductors (including light-emitting diodes (LEDs)).

(1) Any electronics production process in which the etching process uses plasma-generated fluorine atoms and other reactive fluorine-containing fragments, that chemically react with exposed thin-films (e.g., dielectric, metals) or substrate (e.g., silicon) to selectively remove portions of material.

(2) Any electronics production process in which chambers used for depositing thin films are cleaned periodically using plasma-generated fluorine atoms and other reactive fluorine-containing fragments.

(3) Any electronics production process in which wafers are cleaned using plasma generated fluorine atoms or other reactive fluorine-containing fragments to remove residual material from wafer surfaces, including the wafer edge.

(4) Any electronics production process in which the chemical vapor deposition (CVD) process or other manufacturing processes use N\textsubscript{2}O.

(5) Any electronics manufacturing production process in which fluorinated heat transfer fluids are used to cool process equipment, to control temperature during device testing, to clean substrate surfaces and other parts, and for soldering (e.g., vapor phase reflow).


§ 98.91 Reporting threshold.

(a) You must report GHG emissions under this subpart if electronics manufacturing production processes, as defined in §98.90, are performed at your facility and your facility meets the requirements of either §98.2(a)(1) or (a)(2). To calculate total annual GHG emissions for comparison to the 25,000 metric ton CO\textsubscript{2}e per year emission threshold in §98.2(a)(2), follow the requirements of §98.2(b), with one exception. Rather than using the calculation methodologies in §98.93 to calculate emissions from electronics manufacturing production processes, calculate emissions of each fluorinated GHG from electronics manufacturing production processes by using paragraphs (a)(1), (a)(2), or (a)(3) of this section, as appropriate, and then sum the emissions of each fluorinated GHG by using paragraph (a)(4) of this section.

(1) If you manufacture semiconductors or MEMS you must calculate annual production process emissions of each input gas i for threshold applicability purposes using the default emission factors shown in Table I–1 to this subpart and Equation I–1 of this subpart.